

5 é / Descriptions

SOD-323 .> // x J ' ! - } 8 â ' ož  
Silicon Diode in a SOD-323 Plastic Package.

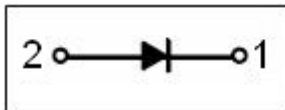
¤ ª / Features

• ¼ , † ½ ož —) í D } ož  
Fast switching diodes. HF Product.

Đ ÷ / Applications

9 4 ' Z Ô ò ož  
Small signal diode.

Ã W ] Ô . / Equivalent Circuit



• Ū - æ / Pinning



PIN1:Cathode      PIN2:Anode

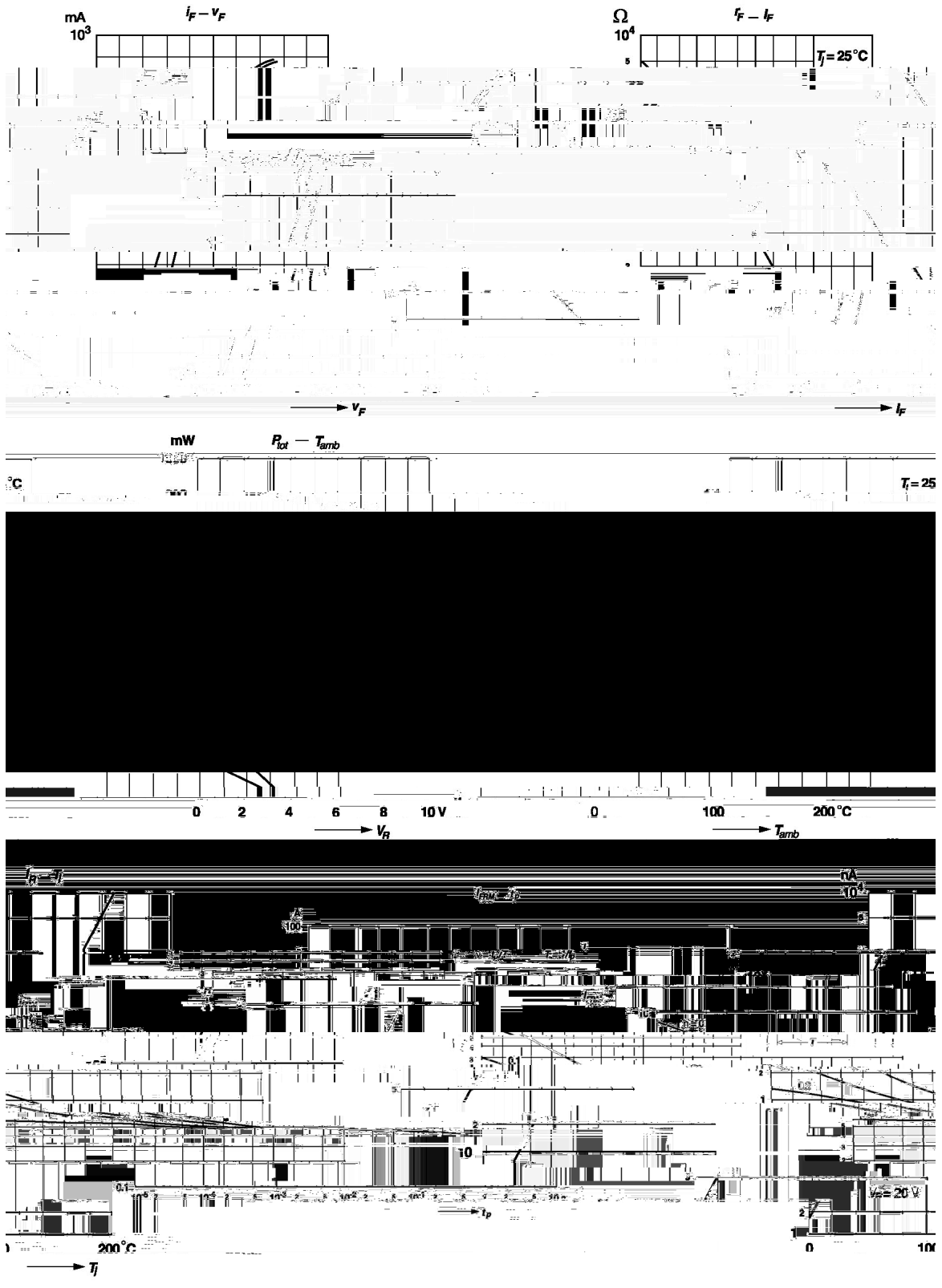
Z Ü B , M V / h<sub>FE</sub> Classifications & Marking

Marking	HA2
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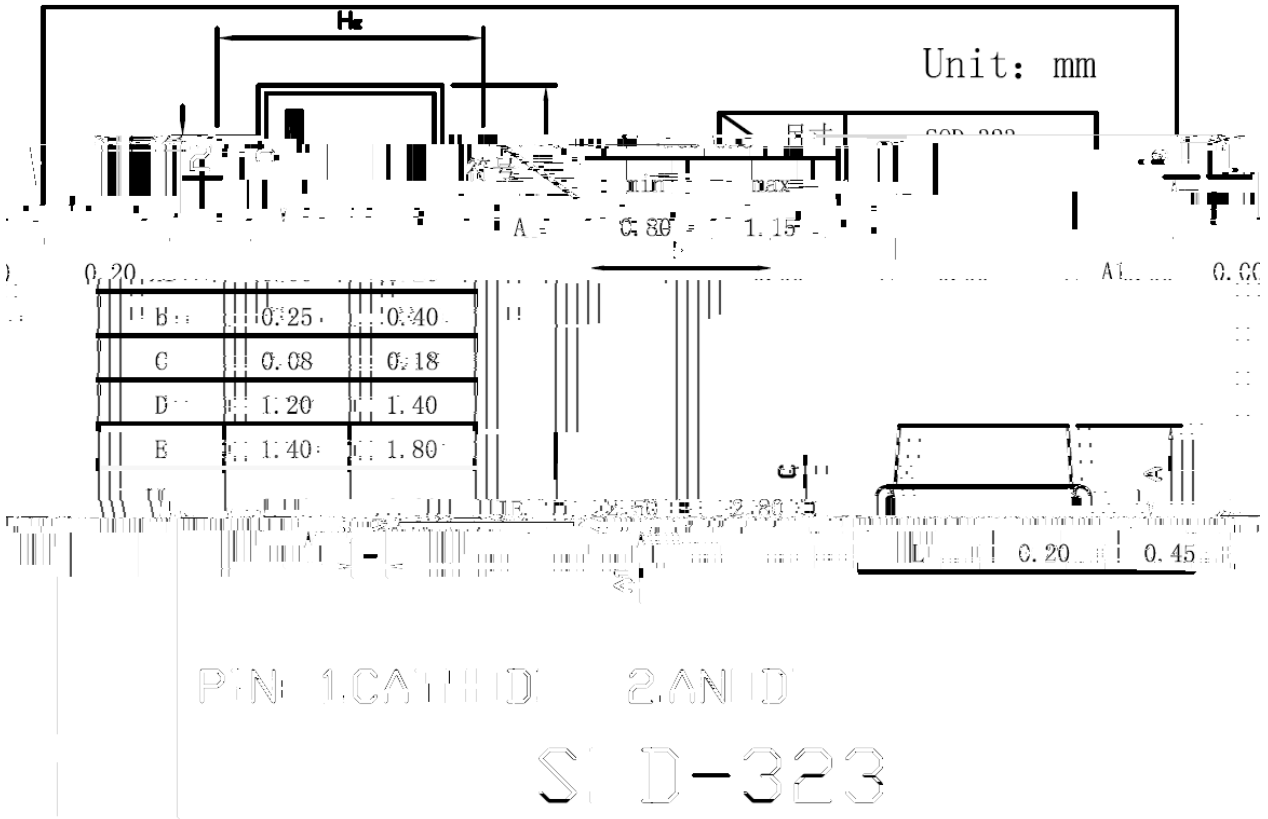
@ f Parameter	... Z Symbol	f › Rating	% y Unit
Reverse Voltage	$V_R$	75	V
Peak Reverse Voltage	$V_{RM}$	100	V
Average Rectified Output Current	$I_O$	150	mA
Forward Continuous Current	$I_{FM}$	300	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM} \text{ } \ddot{A}t=1.0 \text{ s } \ddot{A}$	2.0	A
	$I_{FSM} \text{ } \ddot{A}t=1.0\text{s } \ddot{A}$	1.0	A
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	
Thermal Resistance Junction to Ambient Air	$R_{JA}$	625	/W

@ f Parameter	... Z Symbol	y j Ú ^ Test Conditions	Â 4 › Min	Â ° › Typ	Â Ý › Max	% y Unit
Forward Voltage	$V_F$	$I_F=10\text{mA}$			1.0	V
Instantaneous Reverse Current	$I_R$	$V_R=20\text{V}$			25	nA
		$V_R=75\text{V}$			5	A
		$V_R=20\text{V} \quad T_j=150$			50	A
Capacitance	$C_{tot}$	$V_F=V_R=0\text{V}$			4	pF
Reverse Recovery Time	$t_{rr}$	$I_F=10\text{mA} \quad V_R=6.0\text{V}$ $I_R=1\text{mA} \quad R_L=100$			4	ns
Voltage Rise when Switching On tested	$V_{fr}$	$t_p=0.1 \text{ s} \quad f_p=5\text{to}100\text{kHz}$ Time<30ns			2.5	V
Total Capacitance	$C_T$	$V_R=0 \quad f=1.0\text{MHz}$			2.0	pF

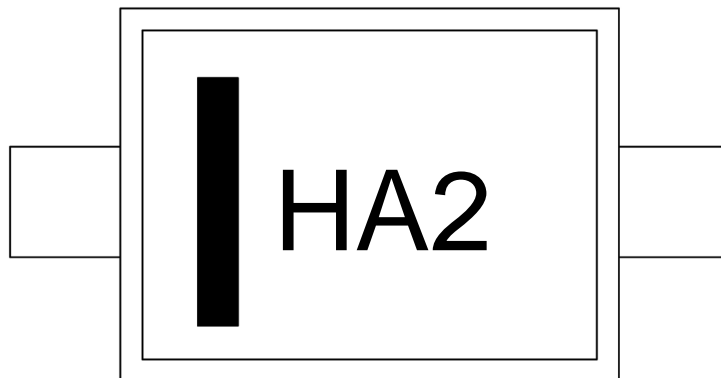
Electrical Characteristic Curve



Ø ≡ ) ϕ / Package Dimensions



, M y f / Marking Instructions



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Note:

H: Company Code.

A2: Product Type.

